

IN THE CLAIMS:

Please amend the claims as follows:

Claim 1 (Previously Presented): An etching mask used for a plasma etching process of a thin film, comprising:

a pass-through aperture for exposing only a surface of the thin film to be etched;

a protruding periphery portion that protrudes at the periphery of the pass-through aperture, and

a blocking portion enclosed by the protruding periphery portion for covering a surface of the thin film other than those that are to be etched.

Claim 2 (Original): The etching mask according to claim 1, wherein the pass-through aperture is covered by a mesh structure provided with a plurality of pass-through holes, each of the plurality of pass-through holes having an area that is smaller than the area of the pass-through aperture.

Claims 3-4 (Canceled).

Claim 5 (Previously Presented): The etching mask according to claim 1, wherein the blocking portion is made of conductive material.

Claim 6 (Previously Presented): The etching mask according to claim 1, wherein the blocking portion is made of metal.

Claims 7-17 (Canceled).

Claim 18 (Previously Presented): The etching mask according to claim 1, wherein the blocking portion is made of electrically conductive material.